

Automotive Gate Driver IC, High and Low Side 600 V, 4.5 A FAN7191-F085, FAD7191

Description

The FAN7191 / FAD7191 is a monolithic high- and low-side gate-driver IC, which can drive high speed MOSFETs and IGBTs that operate up to +600 V. It has a buffered output stage with all NMOS transistors designed for high pulse driving capability and minimum cross-conduction.

ON Semiconductor's high-voltage process and common-mode noise canceling technique provide stable operation of high-drivers under high dV/dt noise circumstances. An advanced level-shift circuit allows high-side gate driver operation up to $V_S = -9.8 \text{ V}$ (typical) for $V_{BS} = 15 \text{ V}$.

The UVLO circuit prevents malfunction when V_{DD} and V_{BS} are lower than the specified threshold voltage.

The high current and low output voltage drop features make this device suitable for controlling direct injection actuators and for use in many automotive DC-DC converter and motor control applications.

Features

- Floating Channel for Bootstrap Operation to +600 V
- 4.5 A Sourcing and 4.5 A Sinking Current Driving Capability
- Common-Mode dV/dt Noise Cancelling Circuit
- Built-in Under-Voltage Lockout for Both Channels
- Matched Propagation Delay for Both Channels
- 3.3 V and 5 V Input Logic Compatible
- Output In-phase with Input
- Enable Pin (For 14–SOP Package Only)
- 14–SOP with Separate Signal and Power Ground for Enhanced Noise Immunity

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- 14–SOP with Increased Clearance for High Voltage Applications
- Automotive Applications, AEC Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Electric and Hybrid Electric Vehicles
- 48 V Mild Hybrid Vehicles
- Automotive High Voltage DC-DC converters
- Motor Control (Fans, Pumps, Compressors)
- Advanced Fuel Injection Systems
- Starter/Alternator
- Electric Power Steering
- MOSFET and IGBT Driver Applications



SOIC8
CASE 751EB



SOIC14 CASE 751EF

ORDERING INFORMATION

Part Number	Package	Shipping [†]
FAN7191MX-F085	8-SOP (751EB)	
FAN7191MX-F085-1	8-SOP (751EB)	2500 / Tape & Reel
FAD7191M1X	14-SOP (751EF)	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

Typical Application Circuit

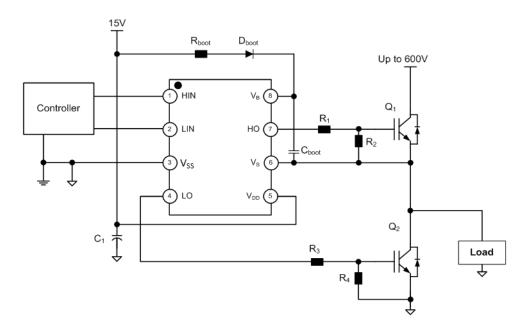


Figure 1. Half-Bridge Application Circuit (8-SOP)

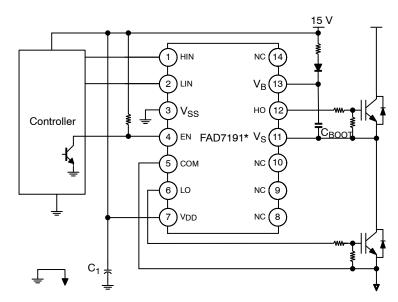


Figure 2. Half-Bridge Application Circuit (14-SOP)

INTERNAL BLOCK DIAGRAM

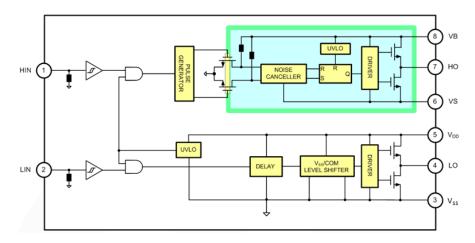


Figure 3. Functional Block Diagram (8-SOP)

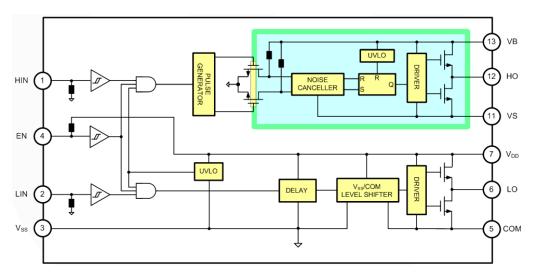


Figure 4. Functional Block Diagram (14-SOP)

Pin Assignment

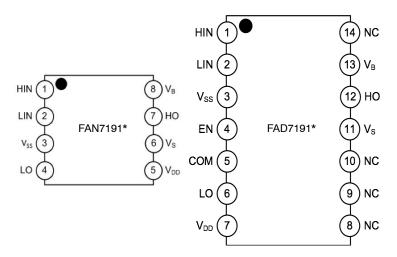


Figure 5. Pin Assignments (Top View)

Table 1. PIN DEFINITIONS

8-Pin	14-Pin	Name	Description
1	1	HIN	Logic Input for High-Side Gate Driver Output
2	2	LIN	Logic Input for Low-Side Gate Driver Output
3	3	V _{SS}	Logic Ground, Power ground for 8-SOP
	4	EN	Enable Input (Internal Pull Up)
	5	COM	Power Ground for 14–SOP, Low–side Driver Return
4	6	LO	Low-Side Driver Output
5	7	V_{DD}	Low-Side and Logic Power Supply Voltage
6	11	V _S	High-Side Floating Supply Return
7	12	НО	High-Side Driver Output
8	13	V _B	High-Side Floating Supply
	8, 9, 10, 14	NC	No Connect

Table 2. ABSOLUTE MAXIMUM RATINGS

(T_A = -40°C to 125°C, unless otherwise specified. V_B, V_{DD} and V_{IN} are referenced to V_{SS})

Symbol	Parameter			Min.	Max.	Unit
V _S	High-side offset voltag	High-side offset voltage VS			V _B + 0.3	V
V _B	High-side floating sup	ply voltage VB		-0.3	625	V
V _{HO}	High-side floating out	put voltage		V _S – 0.3	V _B + 0.3	V
V_{DD}	Low-side and logic-fi	xed supply voltage		-0.3	25	V
COM	Power Ground (14–S0	DP)		V _{DD} – 25	V _{DD} + 0.3	V
V _{IN}	Logic Input voltage (H	Logic Input voltage (HIN, LIN, EN)			V _{DD} + 0.3	V
V_{LO}	Low-Side Output Volta	Low-Side Output Voltage LO (8-SOP)			V _{DD} + 0.3	V
	Low-Side Output Voltage LO (14-SOP)			COM - 0.3	V _{DD} + 0.3	V
T _{pulse} (Note 4)	Minimum Pulse Width			80		ns
d _{VS/dt}	Allowable offset voltage	Allowable offset voltage slew rate			50	V/ns
P _D	Power Dissipation, T _A = 25°C		8-SOP		0.625	W
(Note 1, 2, 3)		14			0.80	W
θ _{JA}	Thermal Resistance, junction-to-ambient		8-SOP		200	°C/W
(Note 1, 2)		Ī	14-SOP		156	°C/W
T _J	Junction temperature	Junction temperature			+150	°C
T _S	Storage temperature			-55	+150	°C
ESD	Electrostatic	Human Body Model,	8-SOP		2500	V
	Discharge Capability	JESD22-A114	14-SOP		2000	
	Charged Device Model,		I, JESD22-C101		2000	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Mounted on $76.2 \times 114.3 \times 1.6$ mm PCB (FR-4 glass epoxy material).
- 2. Refer to the following standards: JESD51-2: Integral circuits thermal test method environmental conditions natural convection. JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages.
- P_D is the power that raises T_J to 150°C for T_A = 25°C. P_D to be derated at higher ambient temperature.
 Minimum input pulse width that guarantee to produce an output pulse. Valid for turn on and turn off pulse width.

Table 3. RECOMMENDED OPERATING CONDITIONS (V_S , V_{DD} and V_{IN} are referenced to V_{SS})

Symbol	Parameter	Min.	Max.	Unit
V _B	High-side floating supply voltage	V _S + 10	V _S + 22	V
V _S	High-side Floating Supply Offset Voltage	6 – V _{BS}	600	V
V _{HO}	High-side Output Voltage	V _S	V _B	V
V_{DD}	Low-side and Logic Supply voltage	10	22	V
	Low-side output voltage (8-SOP)	0	V_{DD}	V
V_{LO}	Low-side output voltage (14-SOP)	СОМ	V_{DD}	V
V _{IN}	Logic input voltage (HIN, LIN, EN)	0	V_{DD}	V
СОМ	Power Ground (14–SOP)	V _{DD} – 22	V_{DD}	V
T _A	Ambient Temperature	-40	+125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 4. ELECTRICAL CHARACTERISTICS

 $(V_{BIAS}~(V_{DD},~V_{BS})$ = 15.0 V, V_S = V_{SS} = COM, T_A = -40°C to 125°C, unless otherwise specified. The V_{IL} , V_{IH} and I_{IN} parameters are referenced to V_{SS} and are applicable to the respective input signals HIN and LIN. The V_O and I_O parameters are referenced to COM (or V_{SS} in case of 8-SOP). V_S and COM (V_{SS} for 8-SOP) are applicable to the respective outputs HO and LO)

Symbol	Characteristic	Condition	Min.	Тур.	Max.	Unit
POWER SUPPLY	SECTION (V _{DD} AND V _{BS})		•	•	•	•
V _{DDUV+} V _{BSUV+}	V _{DD} and V _{BS} Supply Under-Voltage Positive-going Threshold		7.8	8.8	9.8	V
V _{DDUV} - V _{BSUV} -	V _{DD} and V _{BS} Supply Under–Voltage Negative Going Threshold		7.2	8.3	9.1	
V _{DDHYS}	V _{DD} supply under-voltage lockout hysteresis			0.5		
I _{LK}	Offset Supply Leakage Current	V _B = V _S = 600 V			50	μΑ
I _{QBS}	Quiescent V _{BS} Supply Current	V _{IN} = 0 V or 5 V		45	110	
I _{QDD}	Quiescent V _{DD} Supply Current	V _{IN} = 0 V or 5 V		75	150	
I _{PBS}	Operating V _{BS} Supply Current	f _{IN} = 20 kHz, RMS value (See Figure 26)		400	800	μА
I _{PDD}	Operating V _{DD} Supply Current	f _{IN} = 20 kHz, RMS value (See Figure 26)		400	800	
LOGIC INPUT SE	CTION (HIN, LIN, EN)		•	•	•	•
V _{IH}	Logic "1" Input Voltage		2.5			V
V _{IL}	Logic "0" Input Voltage				1.2	
I _{IN+}	Logic "1" Input Bias Current (HIN/LIN)	V _{IN} = 5 V		25	50	μΑ
I _{IN} _	Logic "0" Input Bias Current (HIN/LIN)	V _{IN} = 0 V		1.0	2.0	
I _{EN+}	Enable High Input Bias Current	EN = 5 V	-100	-50	-10	
I _{EN-}	Enable Low Input Bias Current	EN = 0 V	-140	-75	-20	
R _{IN}	Input Pull-down Resistance		100	200		kΩ
GATE DRIVER O	UTPUT SECTION (HO, LO)					
V _{OH}	High-level Output Voltage, V _{BIAS} -V _O	No Load			1.35	V
V _{OL}	Low-level Output Voltage, VO	No Load			35	mV
I _{O+} (Note 5)	Output HIGH, Short-circuit Pulsed Current	$V_O = 0 \text{ V}, V_{IN} = 5 \text{ V} \text{ with }$ PW < 10 μ s	3.5	4.5		Α
I _{O-} (Note 5)	Output LOW Short-circuit Pulsed Current	$V_O = 15 \text{ V}, V_{IN} = 0 \text{ V} \text{ with}$ PW < 10 μs	3.5	4.5		
Vs	Allowable Negative V _S Pin Voltage for HIN Signal Propagation to HO	V _{BS} = 15V		-9.8	-9.0	V
COM-V _{SS} (Note 5)	Allowable COM-V _{SS} ground offset	14-SOP, V _{DD} = 15 V, V _{SS} = 0 V	-7.0			V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Parameters guaranteed by design.

Table 5. DYNAMIC ELECTRICAL CHARACTERISTICS

 $(V_{BIAS}\;(V_{DD},\,V_{BS})=15.0\;V,\,V_{S}\;=V_{SS}=COM=0\;V,\,T_{A}=-40^{\circ}C\;to\;125^{\circ}C,\,C_{LOAD}=1000\;pF\;unless\;otherwise\;specified)$

Symbol	Characteristic	Condition	Min.	Тур.	Max.	Unit
t _{on}	Turn-on Propagation Delay	V _S = 0 V		140	200	ns
t _{off}	Turn-off Propagation Delay	V _S = 0 V		140	200	ns
MT	Delay Matching				55	ns
t _r	Turn-on Rise Time			25	50	ns
t _f	Turn-off Fall Time			25	50	ns

Typical Characteristics

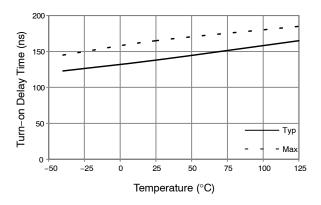


Figure 6. Turn-on Propagation Delay vs. Temperature

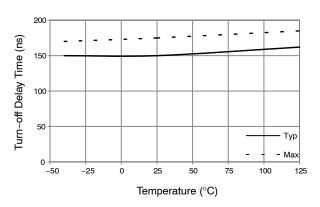


Figure 7. Turn-off Propagation Delay vs. Temperature

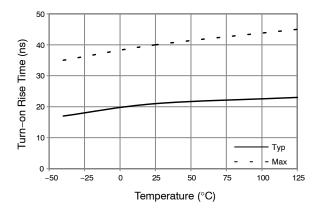


Figure 8. Turn-on Rise Time vs. Temperature

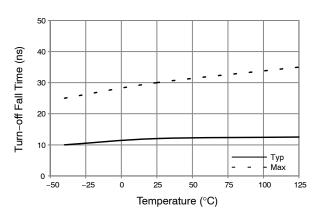


Figure 9. Turn-off Fall Time vs. Temperature

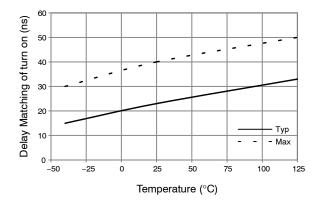


Figure 10. Turn-on Delay Matching vs. Temperature

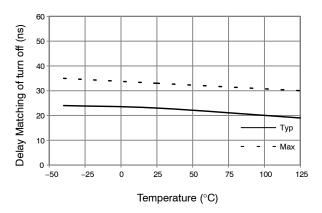
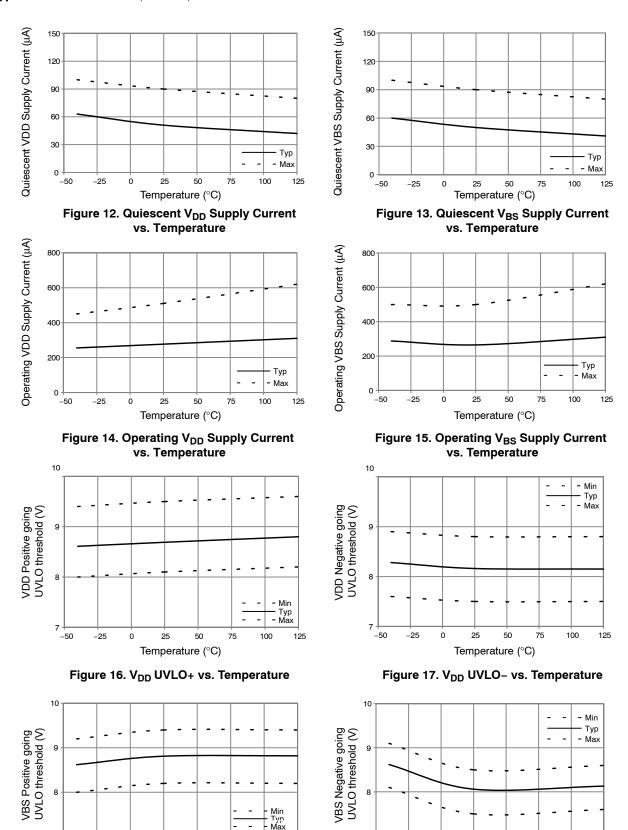


Figure 11. Turn-off Delay Matching vs. Temperature

Typical Characteristics (continued)



Temperature (°C) Figure 18. V_{BS} UVLO+ vs. Temperature

-50

-25

Temperature (°C) Figure 19. V_{BS} UVLO- vs. Temperature

100

125

-50

-25

Typical Characteristics (continued)

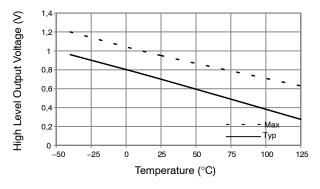
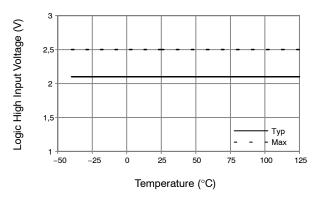


Figure 20. High-Level Output Voltage vs. Temperature

Figure 21. Low-Level Output Voltage vs. Temperature



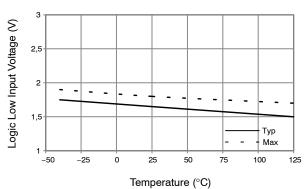
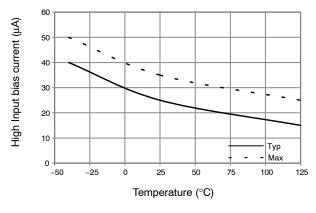


Figure 22. Logic High Input Voltage vs. Temperature

Figure 23. Logic Low Input Voltage vs. Temperature



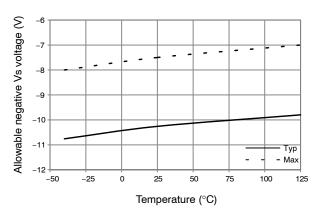


Figure 24. Logic "1" Input Bias Current vs. Temperature

Figure 25. Allowable Negative VS Voltage vs. Temperature

Switching Time Definitions

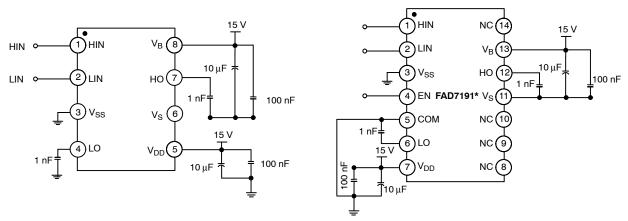


Figure 26. Switching Time Test Circuit

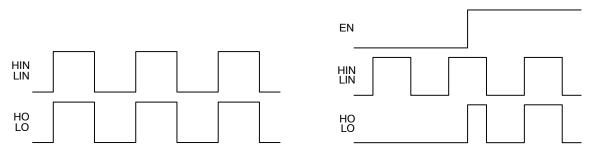


Figure 27. Input / Output Timing Diagram

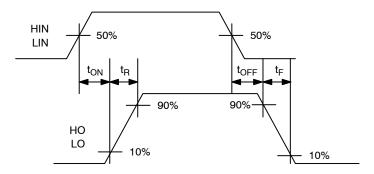


Figure 28. Switching Time Waveform Definitions

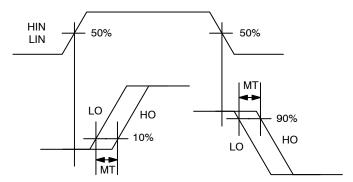
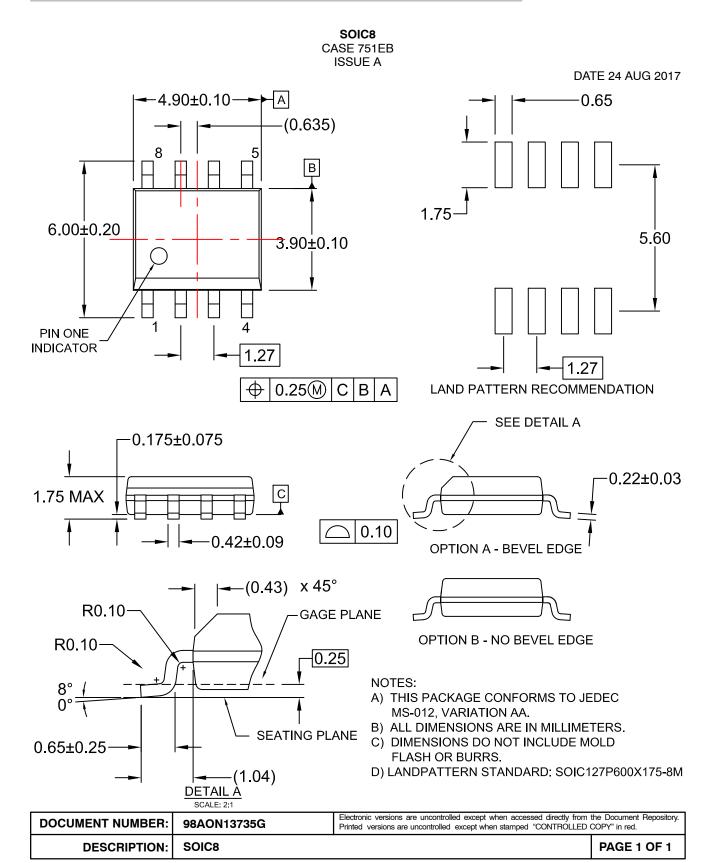


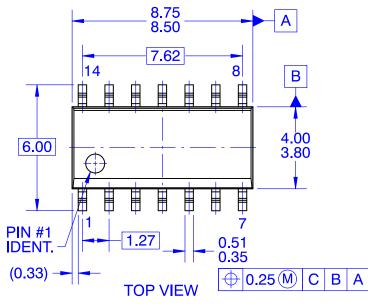
Figure 29. Delay Matching Waveform Definition

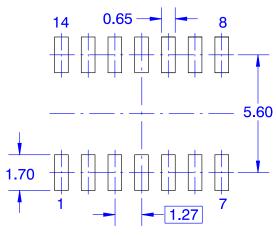


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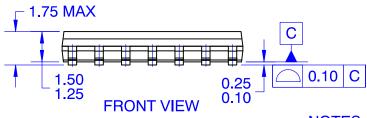
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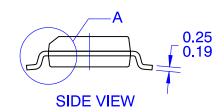
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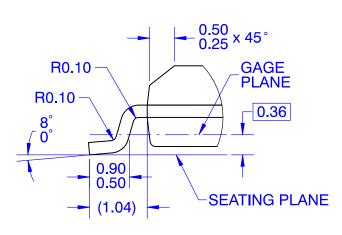
LAND PATTERN RECOMMENDATION





NOTES:

- A. CONFORMS TO JEDEC MS-012, VARIATION AB, ISSUE C
 B. ALL DIMENSIONS ARE IN MILLIMETERS
- C. DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS
- LAND PATTERN STANDARD: SOIC127P600X145-14M
- E. CONFORMS TO ASME Y14.5M, 2009



DETAIL A SCALE 16:1

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